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Jiges Mak 927 a tral f2 9 m f3 3 an ren (en jan 19 0 12 7 a transformed a transformed

Classifying Behavior of the Process Parameter Variations

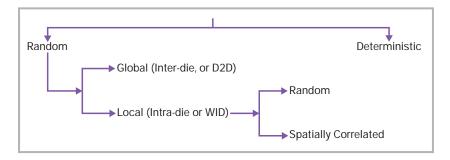


Figure 1: Independent and Correlated Process Parameter Variations in Silicon Photonics

Summarizing the above, process parameter variations in a parameter can be modeled as:

where is the nominal value of the parameter . Last three terms in the above expression represent die-to-die and

The mean and variance of are:

Mean:

m_ĐÔĐ

Variance:

Monte Carlo Process Variation and Corner Analyses in Synopsys OptoCompiler-OptSim

Defining Parameters Using Statistical Expressions

Figure 2: Schematic of a 6-stage lattice filter (a). Each hierarchy comprises of three stages (b) where each stage is implemented as parametric custom photonic block (c)

Defining parameter G via a statistical expression, say, GAUSS(1μ m,0.025 μ m) would imply that gap G follows a Gaussian distribution with 1μ m mean and a 3 deviation of 0.025 μ m relative to the mean. Process correlation can be specified via intermediate variable definitions. For example:

 $G1=GAUSS(0.1\mu m, 0.025\mu m)$

G_wafer_to_wafer = AGAUSS(0.0,0.01 µm)

If G_wafer_to_wafer represents another random variable with zero mean and absolute 3 deviation of 0.01µm, an expression like



Figure 3: Filter response after 3- (upper right) and 6- (lower right) stages of lattice filters accounting for process parameter variations in gap and delay length

Using Sub-Circuit Definitions

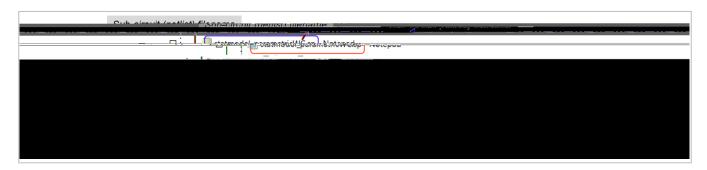


Figure 4: Example of a sub-circuit definition with process parameter variations

illustrated in Figure 5.

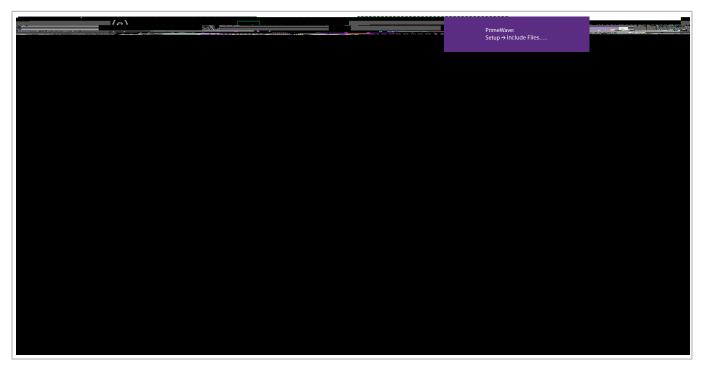


Figure 5: (a) A Mach-Zehnder Interferometer (MZI) comprising of two waveguide sub-circuits (b) including sub-circuit file of Figure 4 during run time and (c) MZI response due to process parameter variations

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